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## Transition metals in silicon

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1093	Ion Mixing Processes. <b>1983</b> , 27, 3		8
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1091	Interstitial transition atom impurities in silicon: electronic structure and lattice relaxation. <b>1984</b> , 17, 6047-6062	1.3	13
1090	Electron paramagnetic resonance on iron-acceptor pairs in silicon. <i>Physical Review B</i> , <b>1984</b> , 30, 4564-4570	3.3	66
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1088	Localization and Magnetism of an Interstitial Iron Impurity in Silicon. <b>1984</b> , 53, 1256-1259		57
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905	Optical and electrical characterization of FeSi <sub>2</sub> epitaxial thin films on silicon substrates. <i>Journal of Applied Physics</i> , <b>1991</b> , 69, 352-357	2.5	131
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889	AC Photovoltaic Images of Thermally Oxidized P-Type Silicon Wafers Contaminated with Metals. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, 2319-2321	1.4	2
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887	Charge-state-dependent diffusion and carrier-emission-limited drift of iron in silicon. <b>1992</b> , 68, 978-981		41
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885	Charge-state-dependent activation energy for diffusion of iron in silicon. <i>Physical Review B</i> , <b>1992</b> , 46, 1882-1885	3.3	25
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826	Evaluation of Ta, Ti and TiW encapsulations for corrosion and diffusion protection of Cu interconnects. <b>1993</b> , 227, 37-43	14
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188	Precipitation of Cu and Ni in n- and p-type Czochralski-grown silicon characterized by photoluminescence imaging. <b>2017</b> , 460, 98-104		3
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- 39 Silicon, solubility data of impurities: group VIB. 1-6
- 38 Silicon, solubility data of impurities: group VIIB. 1-6
- 37 Silicon, solubility data of impurities: group VIII (iron group). 1-10
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- 35 Silicon, solubility data of impurities: group VIII (nickel group). 1-11
- 34 Silicon, solubility data of impurities: group IB. 1-20
- 33 Silicon, solubility data of impurities: group VIII (group IIIA). 1-20

32	Silicon, solubility data of impurities and native point defects: group IVA. 1-16		
31	Silicon, solubility data of impurities: group VA. 1-19		
30	Silicon, distribution coefficients at the melting point. 1-8		
29	Silicon, ionization energies and structural information on impurities: B [B-Zn. 1-6		
28	Silicon, ionization energies and structural information on impurities: Co [Cr-Zn. 1-6		
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